## MBD54DWT1G

## Preferred Device

## Dual Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

## Features

- Extremely Fast Switching Speed
- Low Forward Voltage - 0.35 V @ $\mathrm{I}_{\mathrm{F}}=10 \mathrm{mAdc}$
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $\left(T_{J}=125^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 30 | V |
| Forward Power Dissipation | $\mathrm{P}_{\mathrm{F}}$ |  |  |
| @ $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  | 150 | mW |
| Derate above $25^{\circ} \mathrm{C}$ |  | 1.2 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Forward Current (DC) | $\mathrm{I}_{\mathrm{F}}$ | 200 Max | mA |
| Junction Temperature | $\mathrm{T}_{\mathrm{J}}$ | 125 Max | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{stg}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ON Semiconductor ${ }^{\circledR}$
http://onsemi.com

## 30 VOLTS DUAL HOT-CARRIER DETECTOR AND SWITCHING DIODES


(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :---: | :---: | :---: |
| MBD54DWT1G | SOT-363 <br> (Pb-Free) | $3000 /$ <br> Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

## MBD54DWT1G

ELECTRICAL CHARACTERISTICS $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted) (EACH DIODE)

| Characteristic | Symbol | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Reverse Breakdown Voltage ( $\mathrm{I}_{\mathrm{R}}=10 \mu \mathrm{~A}$ ) | $\mathrm{V}_{(\mathrm{BR}) \mathrm{R}}$ | 30 | - | - | V |
| Total Capacitance ( $\mathrm{V}_{\mathrm{R}}=1.0 \mathrm{~V}, \mathrm{f}=1.0 \mathrm{MHz}$ ) | $\mathrm{C}_{\mathrm{T}}$ | - | 7.6 | 10 | pF |
| Reverse Leakage ( $\mathrm{V}_{\mathrm{R}}=25 \mathrm{~V}$ ) | $\mathrm{I}_{\mathrm{R}}$ | - | 0.5 | 2.0 | $\mu \mathrm{Adc}$ |
| Forward Voltage ( $\mathrm{l}_{\mathrm{F}}=0.1 \mathrm{mAdc}$ ) | $\mathrm{V}_{\mathrm{F}}$ | - | 0.22 | 0.24 | Vdc |
| Forward Voltage ( $\mathrm{I}_{\mathrm{F}}=30 \mathrm{mAdc}$ ) | $\mathrm{V}_{\mathrm{F}}$ | - | 0.41 | 0.5 | Vdc |
| Forward Voltage ( $\mathrm{l}_{\mathrm{F}}=100 \mathrm{mAdc}$ ) | $V_{F}$ | - | 0.52 | 1.0 | Vdc |
| Reverse Recovery Time ( $\left.\mathrm{I}_{\mathrm{F}}=\mathrm{I}_{\mathrm{R}}=10 \mathrm{mAdc}, \mathrm{I}_{\mathrm{R}(\mathrm{REC})}=1.0 \mathrm{mAdc}\right)$ (Figure 1) | $\mathrm{t}_{\mathrm{rr}}$ | - | - | 5.0 | ns |
| Forward Voltage ( $\mathrm{l}_{\mathrm{F}}=1.0 \mathrm{mAdc}$ ) | $\mathrm{V}_{\mathrm{F}}$ | - | 0.29 | 0.32 | Vdc |
| Forward Voltage ( $\mathrm{I}_{\mathrm{F}}=10 \mathrm{mAdc}$ ) | $\mathrm{V}_{\mathrm{F}}$ | - | 0.35 | 0.40 | Vdc |
| Forward Current (DC) | $\mathrm{I}_{\mathrm{F}}$ | - | - | 200 | mAdc |
| Repetitive Peak Forward Current | $\mathrm{I}_{\text {FRM }}$ | - | - | 300 | mAdc |
| Non-Repetitive Peak Forward Current (t < 1.0 s ) | $\mathrm{I}_{\text {FSM }}$ | - | - | 600 | mAdc |



Notes: 1. A $2.0 \mathrm{k} \Omega$ variable resistor adjusted for a Forward Current $\left(\mathrm{I}_{\mathrm{F}}\right)$ of 10 mA .
2. Input pulse is adjusted so $\mathrm{I}_{\mathrm{R} \text { (peak) }}$ is equal to 10 mA .
3. $t_{p}$ " $t_{r r}$

Figure 1. Recovery Time Equivalent Test Circuit



Figure 4. Total Capacitance


## CASE 419B-02

ISSUE Y
*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SIDE VIEW


END VIEW


## RECOMMENDED SOLDERING FOOTPRINT*

NOTES:
. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS B AND C APPLY TO THE FLAT SECTION OF THE DIMENSIONS b AND C APPLY TO THE FLAT SEC
LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

|  | MILLIMETERS |  |  | INCHES |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | --- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC |  |  | 0.026 BSC |  |  |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC |  |  | 0.006 BSC |  |  |
| aaa | 0.15 |  |  | 0.006 |  |  |
| bbb | 0.30 |  |  | 0.012 |  |  |
| ccc | 0.10 |  |  | 0.004 |  |  |
| ddd | 0.10 |  |  | 0.004 |  |  |

GENERIC MARKING DIAGRAM*


XXX = Specific Device Code
M = Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{\nabla}$ ", may or may not be present.


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